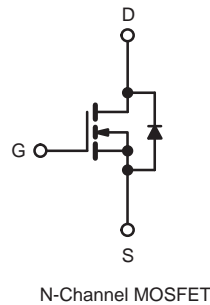
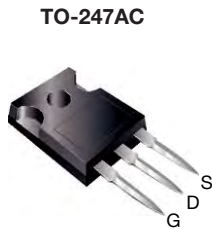


## N-Channel 650 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY		
V <sub>DS</sub> (V) at T <sub>J</sub> max.	650	
R <sub>DS(on)</sub> max. at 25 °C (Ω)	V <sub>GS</sub> = 10 V	0.106
Q <sub>g</sub> max. (nC)	273	
Q <sub>gs</sub> (nC)	46	
Q <sub>gd</sub> (nC)	79	
Configuration	Single	



### FEATURES

- Low Figure-of-Merit (FOM) R<sub>on</sub> x Q<sub>g</sub>
- Low Input Capacitance (C<sub>iss</sub>)
- Reduced Switching and Conduction Losses
- Ultra Low Gate Charge (Q<sub>g</sub>)
- Avalanche Energy Rated (UIS)



**RoHS**  
COMPLIANT

### APPLICATIONS


- Server and Telecom Power Supplies
- Switch Mode Power Supplies (SMPS)
- Power Factor Correction Power Supplies (PFC)
- Lighting
  - High-Intensity Discharge (HID)
  - Fluorescent Ballast Lighting
- Industrial
  - Welding
  - Induction Heating
  - Motor Drives
  - Battery Chargers
  - Renewable Energy
  - Solar (PV Inverters)

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V <sub>DS</sub>	650	V
Gate-Source Voltage	V <sub>GS</sub>	± 20	
Gate-Source Voltage AC (f > 1 Hz)		30	
Continuous Drain Current (T <sub>J</sub> = 150 °C)	V <sub>GS</sub> at 10 V	T <sub>C</sub> = 25 °C	A
		T <sub>C</sub> = 100 °C	
Pulsed Drain Current <sup>a</sup>	I <sub>DM</sub>	139	
Linear Derating Factor		3.3	W/°C
Single Pulse Avalanche Energy <sup>b</sup>	E <sub>AS</sub>	1410	mJ
Maximum Power Dissipation	P <sub>D</sub>	417	W
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C
Drain-Source Voltage Slope	dV/dt	T <sub>J</sub> = 125 °C	V/ns
Reverse Diode dV/dt <sup>d</sup>		9	
Soldering Recommendations (Peak Temperature) <sup>c</sup>	for 10 s	300	°C

### Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- V<sub>DD</sub> = 50 V, starting T<sub>J</sub> = 25 °C, L = 28.2 mH, R<sub>g</sub> = 25 Ω, I<sub>AS</sub> = 10 A.
- 1.6 mm from case.
- I<sub>SD</sub> ≤ I<sub>D</sub>, dI/dt = 100 A/μs, starting T<sub>J</sub> = 25 °C.

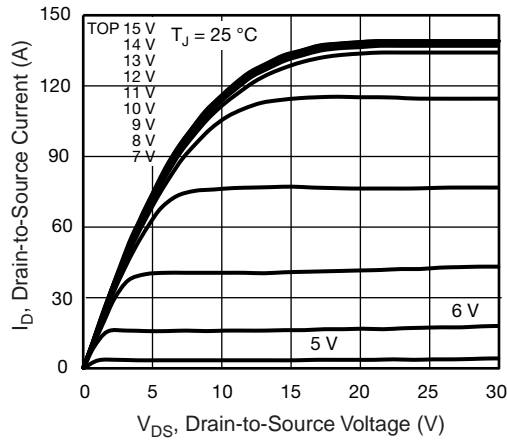
THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	$R_{thJA}$	-	40	°C/W
Maximum Junction-to-Case (Drain)	$R_{thJC}$	-	0.3	

SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
<b>Static</b>							
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		650	-	-	V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$ , $I_D = 1\text{ mA}$		-	0.70	-	V/°C
Gate-Source Threshold Voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		2	-	4	V
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 20\text{ V}$		-	-	$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 650\text{ V}, V_{GS} = 0\text{ V}$		-	-	1	$\mu\text{A}$
		$V_{DS} = 520\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$		-	-	25	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 24\text{ A}$	-	0.100	0.106	$\Omega$
Forward Transconductance	$g_{fs}$	$V_{DS} = 30\text{ V}, I_D = 24\text{ A}$		-	16.7	-	S
<b>Dynamic</b>							
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V},$ $V_{DS} = 100\text{ V},$ $f = 1\text{ MHz}$		-	5682	-	pF
Output Capacitance	$C_{oss}$			-	251	-	
Reverse Transfer Capacitance	$C_{rss}$			-	1	-	
Effective Output Capacitance, Energy Related <sup>a</sup>	$C_{o(er)}$	$V_{DS} = 0\text{ V to } 520\text{ V}, V_{GS} = 0\text{ V}$		-	192	-	pF
Effective Output Capacitance, Time Related <sup>b</sup>	$C_{o(tr)}$			-	665	-	
Total Gate Charge	$Q_g$	$V_{GS} = 10\text{ V}$	$I_D = 24\text{ A}, V_{DS} = 520\text{ V}$	-	182	273	nC
Gate-Source Charge	$Q_{gs}$			-	46	-	
Gate-Drain Charge	$Q_{gd}$			-	79	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 520\text{ V}, I_D = 6\text{ A},$ $V_{GS} = 10\text{ V}, R_g = 9.1\text{ }\Omega$		-	47	94	ns
Rise Time	$t_r$			-	87	131	
Turn-Off Delay Time	$t_{d(off)}$			-	156	234	
Fall Time	$t_f$			-	103	206	
Gate Input Resistance	$R_g$	$f = 1\text{ MHz}, \text{ open drain}$		-	0.64	-	$\Omega$
<b>Drain-Source Body Diode Characteristics</b>							
Continuous Source-Drain Diode Current	$I_S$	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	38	A
Pulsed Diode Forward Current	$I_{SM}$			-	-	139	
Diode Forward Voltage	$V_{SD}$	$T_J = 25\text{ }^\circ\text{C}, I_S = 24\text{ A}, V_{GS} = 0\text{ V}$		-	0.9	1.2	V
Reverse Recovery Time	$t_{rr}$	$T_J = 25\text{ }^\circ\text{C}, I_F = I_S = 24\text{ A},$ $dI/dt = 100\text{ A}/\mu\text{s}, V_R = 25\text{ V}$		-	753	1506	ns
Reverse Recovery Charge	$Q_{rr}$			-	14	28	$\mu\text{C}$
Reverse Recovery Current	$I_{RRM}$			-	28	-	A

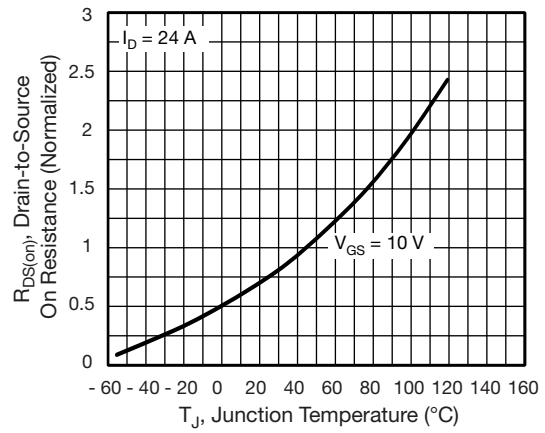
**Notes**

- a.  $C_{oss(er)}$  is a fixed capacitance that gives the same energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$ .
- b.  $C_{oss(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$ .

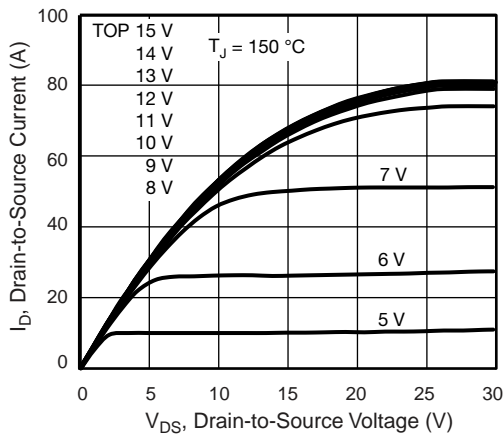
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



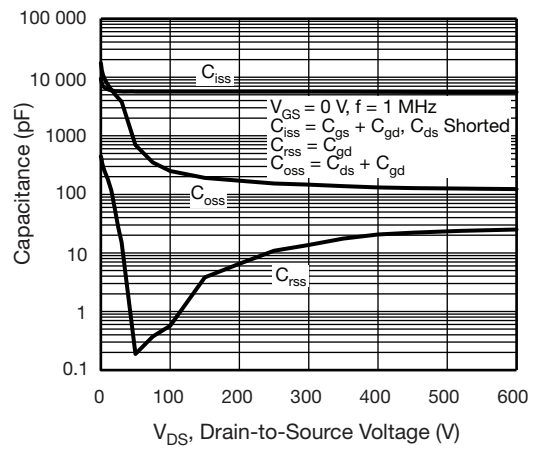
**Fig. 1 - Typical Output Characteristics**



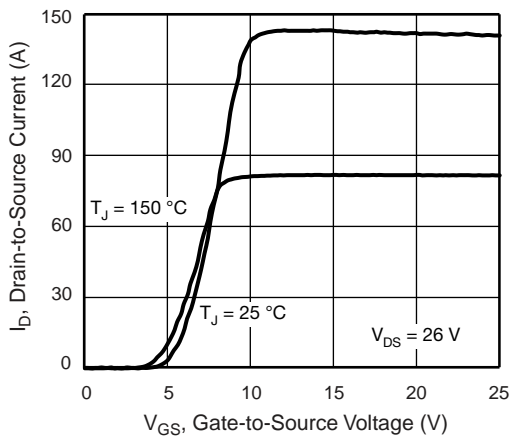
**Fig. 4 - Normalized On-Resistance vs. Temperature**



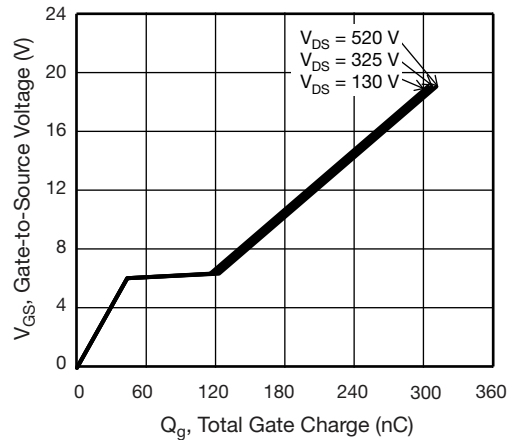
**Fig. 2 - Typical Output Characteristics**



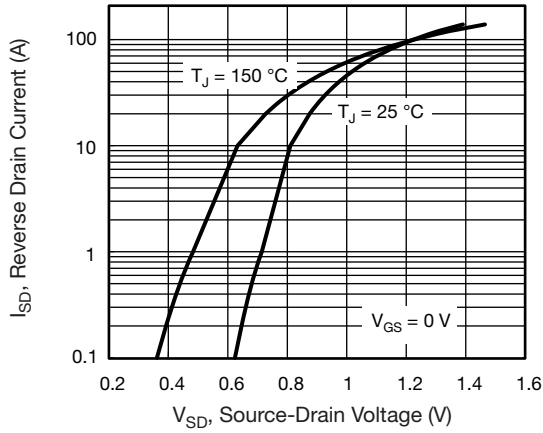
**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**



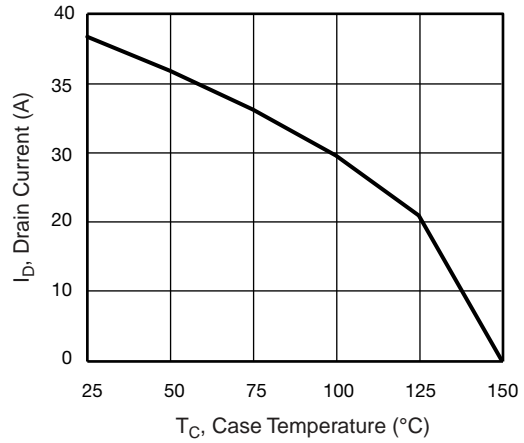
**Fig. 3 - Typical Transfer Characteristics**



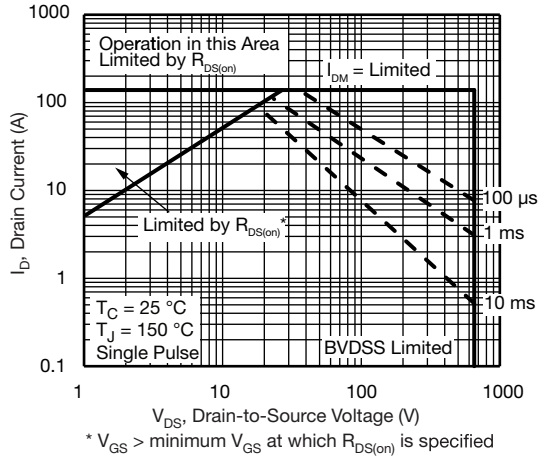
**Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage**



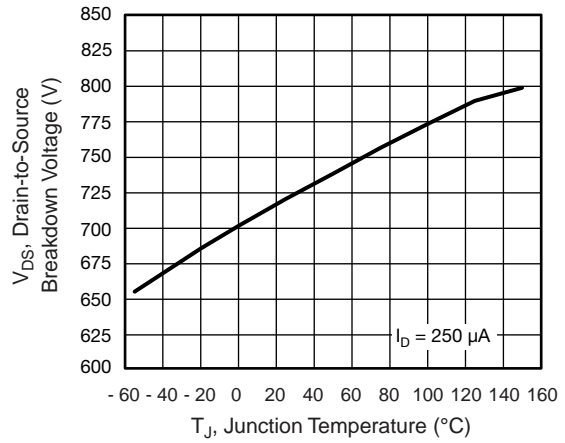
**Fig. 7 - Typical Source-Drain Diode Forward Voltage**



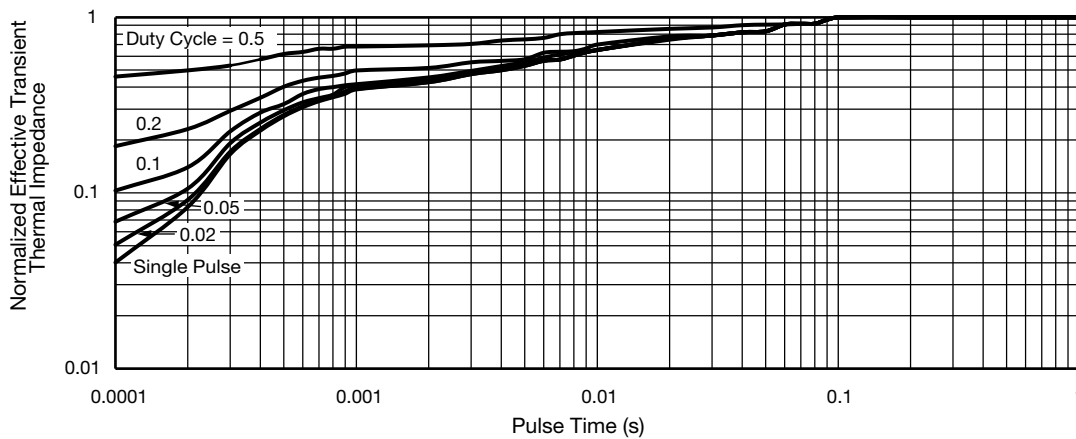
**Fig. 9 - Maximum Drain Current vs. Case Temperature**



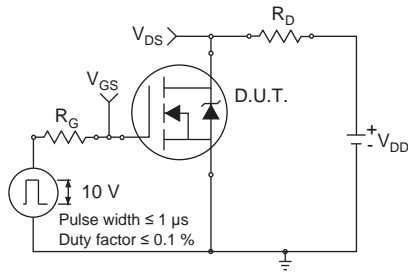
**Fig. 8 - Maximum Safe Operating Area**



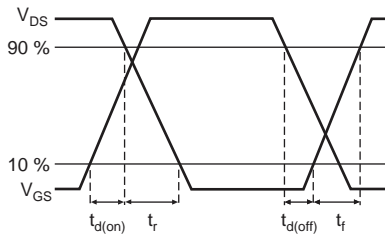
**Fig. 10 - Temperature vs. Drain-to-Source Voltage**



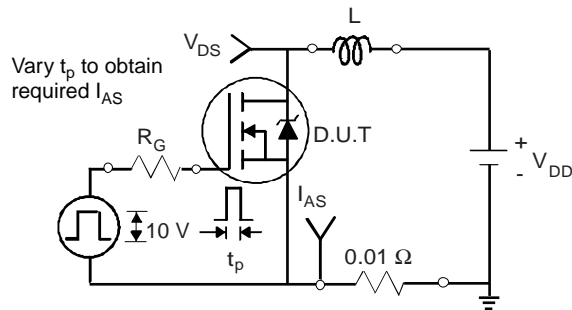
**Fig. 11 - Normalized Thermal Transient Impedance, Junction-to-Case**



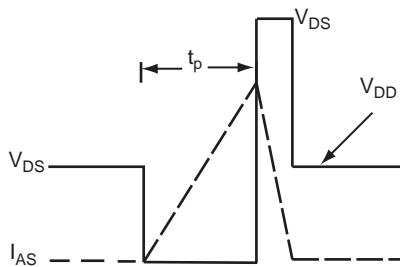
**Fig. 12 - Switching Time Test Circuit**



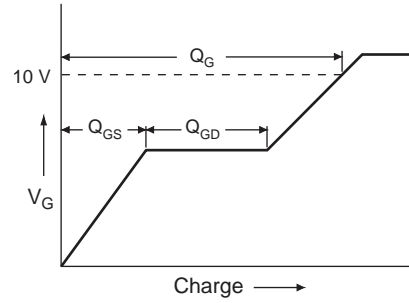
**Fig. 13 - Switching Time Waveforms**



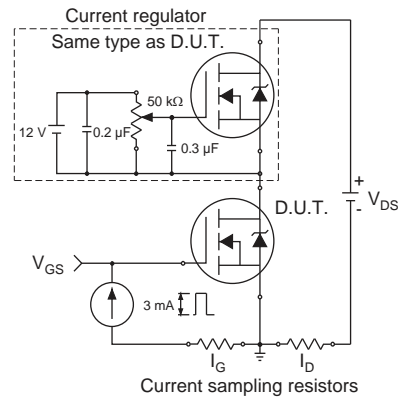
**Fig. 14 - Unclamped Inductive Test Circuit**



**Fig. 15 - Unclamped Inductive Waveforms**

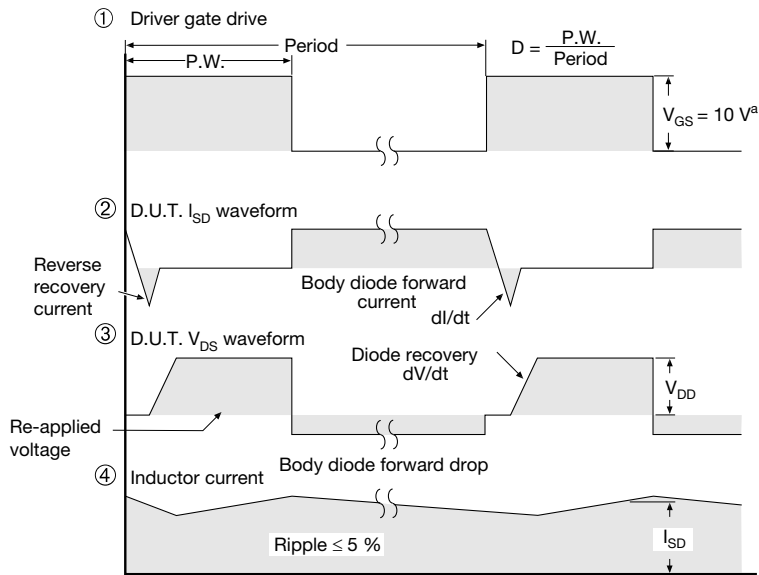
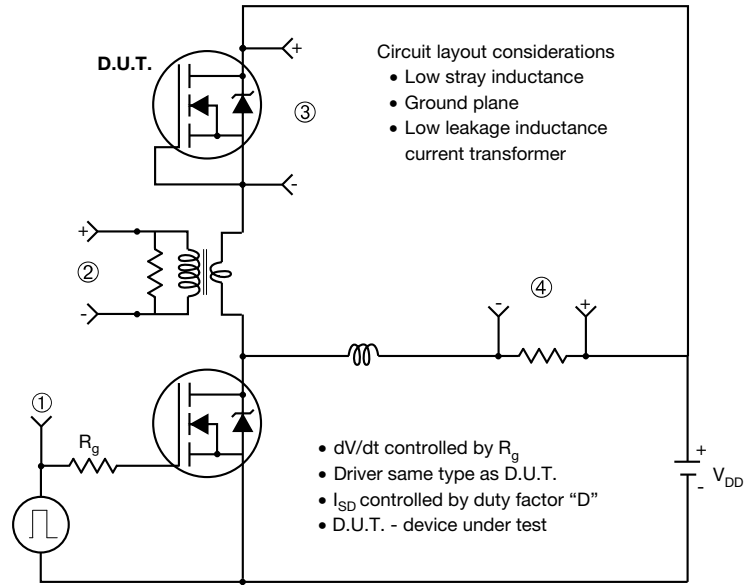


**Fig. 16 - Basic Gate Charge Waveform**



**Fig. 17 - Gate Charge Test Circuit**

**Peak Diode Recovery dV/dt Test Circuit**

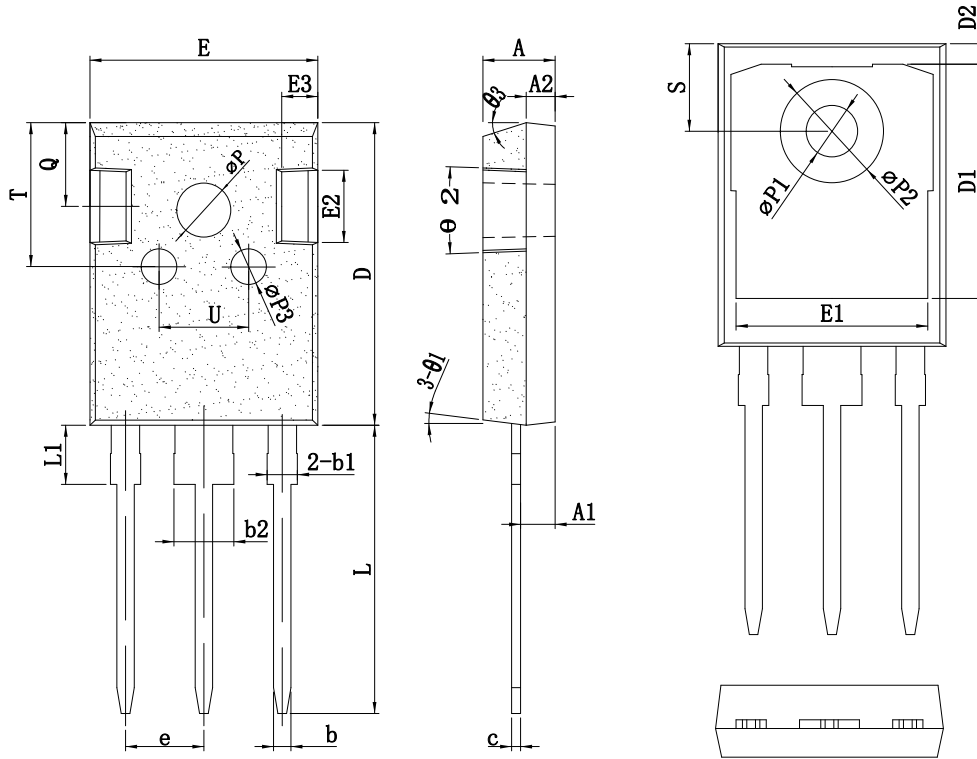


**Note**

a.  $V_{GS} = 5 V$  for logic level devices

**Fig. 18 - For N-Channel**

**TO-247\_3L PACKAGE OUTLINE**



COMMON DIMENSIONS  
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	TYP	MAX	SYMBOL	MIN	TYP	MAX
A	4.60	5.00	5.40	e	2.10	5.44	5.70
A1	2.10	2.41	2.70	L	19.00	19.98	21.00
A2	1.70	2.00	2.30	L1	-	-	4.50
b	1.00	1.20	1.40	$\Phi P$	3.30	3.70	4.00
b1	1.80	2.10	2.40	$\Phi P1$	3.25	3.55	3.85
b2	2.80	3.10	3.40	$\Phi P2$	6.80	7.18	7.60
C	0.45	0.60	0.75	$\Phi P3$	2.30	2.50	3.30
D	19.00	21.00	23.00	Q	5.50	5.80	6.30
D1	16.00	16.55	17.00	S	5.60	6.15	6.30
D2	0.95	1.20	1.45	T	9.50	10.00	10.50
E	15.70	15.80	16.50	U	6.00	-	8.00
E1	12.80	13.25	13.70	$\theta 1$	5°	7°	9°
E2	4.20	5.00	5.30	$\theta 2$	1°	3°	5°
E3	2.20	2.50	2.80	$\theta 3$	13°	15°	17°

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